U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.310US0	10/600,259
	Applicant(s)	
(Use several sheets if necessary)	Jeffrey Lutze et al.	
	Filing Date	Group
	06/20/03	Unknown

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TL	001	6,529,410	3/2003	Han et al.			
	002	6,295,227	9/2001	Sakui et al.			
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✓	008	5,343,063	8/30/1994	Yuan et al.			

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TL	009	U.S. 2002/0093073	7/18/2002	Mori et al.			
TL	010	U.S. 2004/0070021	4/15/2004	Yuan, Jack H.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

TL	011	International Search Report, PCT/US03/32119 filed 08/10/2003
	012	U.S. Patent Application No. 09/667,344 Yuan et al. 9/22/2000
	013	Aritome, Seiichi, "Advanced Flash Memory Technology and Trends for File Storage Application," IEDM Technical Digest, International Electronic Devices Meeting, IEEE, San Francisco, California, December 10-13. 2000, pp 33.1.1-33.1.4.
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Examiner	Date Considered 8/25/09

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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